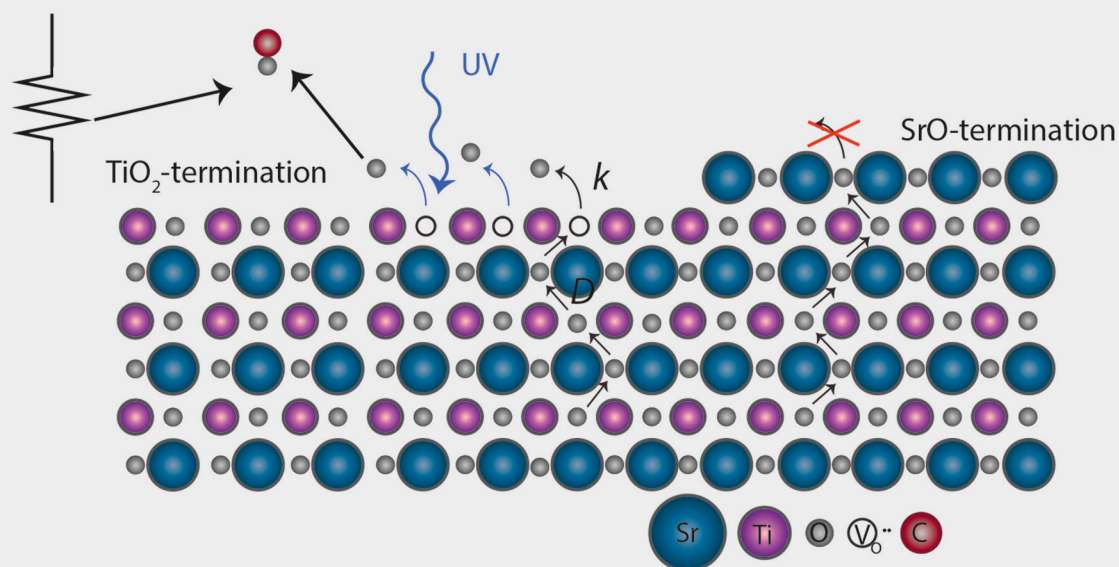




Defect engineering in oxide thin films

Felix V. E. Hensling

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